

Never stop thinking

TLE4906-3K

High Precision Hall-Effect Switch

Datasheet

Rev 1.0, 2010-12

Sensors

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TLE4906-3K High Precision Hall Effect Switch

Revision History: 2010-12, Rev 1.0

Previous	Previous Version:					
Page	Subjects (major changes since last revision)					

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High Precision Hall-Effect Switch

TLE4906-3K



1 Product Description

1.1 Overview

The TLE4906-3K is a high precision Hall effect switch with highly accurate switching thresholds for operating temperatures up to 150° C.

1.2 Features

- 2.7V to 24V supply voltage
- Operation from unregulated power supply
- High sensitivity and high stability of the magnetic switching points
- High resistance to mechanical stress by Active Error Compensation
- Reverse battery protection (-18V)
- Superior temperature stability
- Low jitter (typ. 1µs)
- High ESD performance (± 4kV HBM)
- Digital output signal
- SMD package SC59 (SOT23 compatible)

1.3 Target Applications

Target applications for TLE4906-3K are all automotive applications which require a high precision Hall switch for position sensing with a operating temperature range from -40°C to +150°C. The TLE4906-3K is a unipolar Hall switch which is actuated with the south pole of a magnet. A magnetic field above the threshold B_{OP} switches the output to low (output transistor ON) and a magnetic field below the release point B_{RP} back to high (transistor OFF).

Product Name	Product Type	Ordering Code	Package
TLE4906-3K	Unipolar Hall Switch	SP000868844	SC59



2 Functional Description

2.1 General

The TLE4906-3K is an integrated circuit Hall-effect sensor designed specifically for highly accurate applications. Precise magnetic switching points and high temperature stability are achieved by active compensation circuits and chopper techniques on chip.

2.2 Pin Configuration (top view)

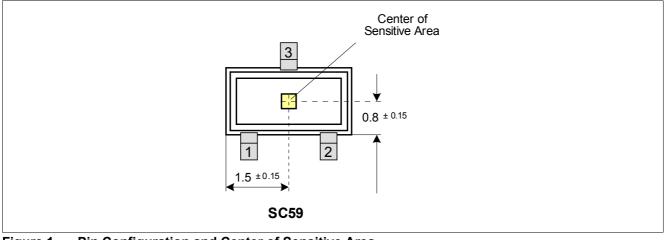


Figure 1 Pin Configuration and Center of Sensitive Area

2.3 Pin Description

Table 1Pin Description SC59

Pin No.	Symbol	Function	Comment
1	V _{DD}	Supply voltage	
2	Q	Output	
3	GND	Ground	



TLE4906-3K

Functional Description

2.4 Block Diagram

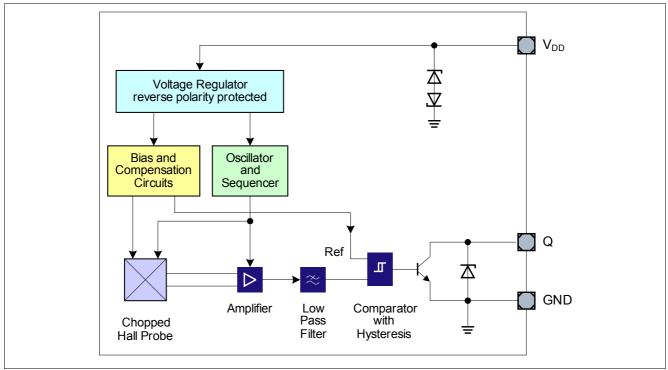


Figure 2 Functional Block Diagram

2.5 Functional Block Description

The chopped Hall IC Switch comprises a Hall probe, bias generator, compensation circuits, oscillator and output transistor.

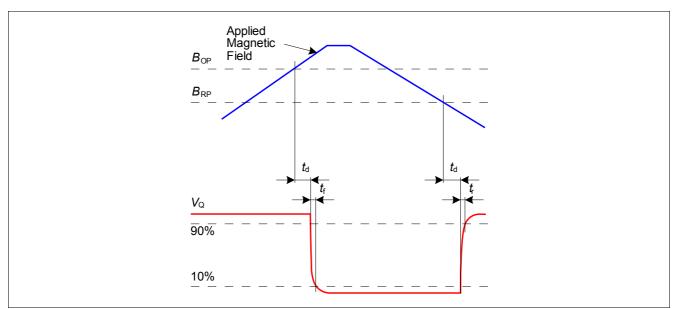
The bias generator provides currents for the Hall probe and the active circuits. Compensation circuits stabilize the temperature behavior and reduce technology variations.

The Active Error Compensation rejects offsets in signal stages and the influence of mechanical stress to the Hall probe caused by molding and soldering processes and other thermal stresses in the package.

This chopper technique together with the threshold generator and the comparator ensure high accurate magnetic switching points.



Functional Description





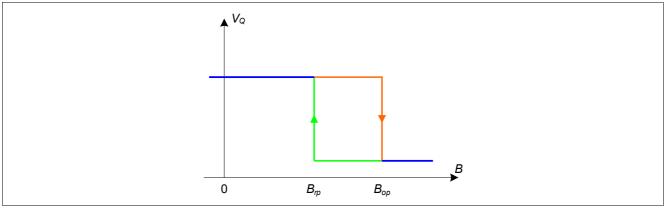


Figure 4 Output Signal



Functional Description

2.6 Application circuit

It is recommended to use a series resistor R_S with 200 Ω and a capacitor of C_{DD} = 4.7nF for protection against overvoltage and transients on the supply line. A capacitor C_Q at the Q pin protects the IC from disturbances coupled to the output. A pull-up resistor R_Q is also required for the output pin Q.

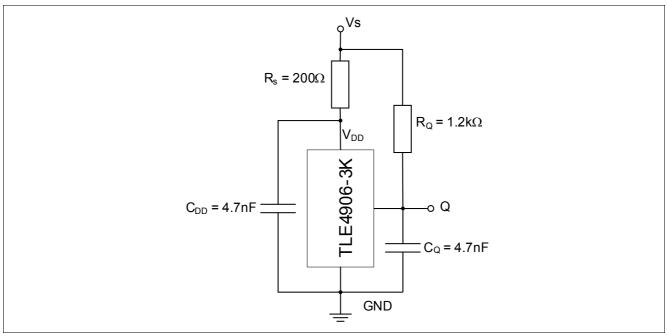


Figure 5 Application circuit



3.1 Absolute Maximum Ratings

Table 2 Absolute Maximum Rating Parameters

T_i = -40°C to 150°C

Parameter	Symbol	Lim	it Values	Unit	Note / Test Condition	
		Min.	Max.	1		
Supply voltage	V _{DD}	-18	18	V		
	Vs	-18	24		for 1h, $R_S \ge 200\Omega$	
	Vs	-18	26		for 5min, $R_S \ge 200\Omega$	
Supply current through	I _{DD}	-50	50	mA		
protection device						
Output voltage	V _Q	-0.7	18	V		
	~	-0.7	26		for 5min @ 1.2k Ω pull up	
Continuous output current	I _Q	-50	50	mA		
Junction temperature	Tj	_	155	°C	for 2000h (not additive)	
	j	_	165		for 1000h (not additive)	
		_	175		for 168h (not additive)	
		-	195		for 3 x 1h (additive)	
Storage temperature	Ts	-40	150	°C		
Magnetic flux density	В	_	unlimited	mT		

Note: Stresses above the max. values listed here may cause permanent damage to the device. Exposure to absolute maximum rating conditions for extended periods may affect device reliability. Maximum ratings are absolute ratings; exceeding only one of these values may cause irreversible damage to the integrated circuit.

Table 3 ESD Protection¹⁾

Parameter	Symbol	Lim	it Values	Unit	Note / Test Condition	
		Min.	Max.			
ESD Voltage	V _{ESD}		±4	kV	HBM, R = 1.5kΩ, C = 100pF T _A = 25°C	

 Human Body Model (HBM) tests according to: EOS/ESD Association Standard S5.1-1993 and Mil. Std. 883D method 3015.7



3.2 Operating Range

The following operating conditions must not be exceeded in order to ensure correct operation of the TLE4906-3K . All parameters specified in the following sections refer to these operating conditions unless otherwise mentioned.

Table 4 Operating Conditions Parameters

Parameter	Symbol	Values			Unit	Note / Test Condition	
		Min.	Тур.	Max.			
Supply voltage	V _{DD}	2.7		18	V		
Output voltage	V _Q	-0.7		18	V		
Junction temperature	Tj	-40		150	°C		
Output current	IQ	0		20	mA		





3.3 Electrical and Magnetic Characteristics

Product characteristics involve the spread of values guaranteed within the specified voltage and ambient temperature range. Typical characteristics are the median of the production.

Parameter	Symbol	Values			Unit	Note / Test Condition	
		Min.	Тур.	Max.			
Supply current	I _{DD}	2	4	6	mA	V _{DD} = 2.7V 18V	
Reverse current	I _{SR}	0	0.2	1	mA	V _{DD} = -18V	
Output saturation voltage	V _{QSAT}	-	0.3	0.6	V	I _Q = 20mA	
Output leakage current	I _{QLEAK}	-	0.05	10	μA	for $V_Q = 18V$	
Output fall time	t _f	-	0.02	1	μs	R_{Q} = 1.2kΩ; C_{Q} = 50pF	
Output rise time	t _r	-	0.4	1	μs	see Figure 3	
Chopper frequency	f _{osc}	-	320	-	kHz		
Switching frequency	f _{sw}	0	-	15 ²⁾	kHz		
Delay time ³⁾	t _d	-	13	-	μs		
Output jitter ⁴⁾	t _{QJ}	-	1	-	μs _{RMS}	typical value for square wave signal with 1kHz	
Power-on time ⁵⁾	t _{PON}	-	13	-	μs	$V_{DD} \ge 2.7V$	
Thermal resistance ⁶⁾	R _{thJA}	-	100	-	K/W	SC59	

 Table 5
 General Electrical Characteristics¹⁾

1) over operating range, unless otherwise specified. Typical values correspond to V_{DD} = 12V and T_A = 25°C

2) To operate the sensor at the max. switching frequency, the value of the magnetic signal amplitude must be 1.4 times higher than for static fields. This is due to the -3dB corner frequency of the low pass filter in the signal path.

3) Systematic delay between magnetic threshold reached and output switching.

4) Jitter is the unpredictable deviation of the output switching delay.

5) Time from applying $V_{DD} \ge 2.7V$ to the sensor until the output state is valid.

6) Thermal resistance from junction to ambient.

Calculation of the ambient temperature:

e.g. for V_{DD} = 12.0V, I_{DDtyp} = 4mA, V_{QSATtyp} = 0.3V and I_Q = 20mA Power dissipation P_{DIS} = 54.0mW In T_A = T_j - (R_{thJA} x P_{DIS}) = 175°C - (100K/W x 0.054W) Resulting max. ambient temperature: T_A = 169.6°C



Parameter	Symbol	T _i [°C]	Values			Unit	Note / Test Condition
		-	Min.	Тур.	Max.		
Operating point	B _{OP}	-40	21.6	30.2	38.8	mT	
	0.	25	20.0	28.0	36.0		
		150	16.8	23.8	30.8		
Release point	B _{RP}	-40	17.1	24.2	31.2	mT	
		25	15.9	22.5	29.1		
		150	13.3	19.1	24.9		
Hysteresis	B _{HYS}	-40	4.4	6.0	7.4	mT	
		25	4.1	5.5	6.9		
		150	3.5	4.7	5.9		
Temperature compensation of magnetic thresholds	T _C		-	-1200	-	ppm/°C	
Repeatability of magnetic thresholds ²⁾	B _{REP}		-	20	-	μT_{RMS}	typ. value for ∆B/∆t > 12mT/ms

Table 6Magnetic Characteristics1)

1) over operating range, unless otherwise specified. Typical values correspond to V_{DD} = 12V and T_A = 25°C.

2) B_{REP} is equivalent to the noise constant

Note: Typical characteristics specify mean values expected over the production spread

Field Direction Definition

Positive magnetic fields are defined with the south pole of the magnet to the branded side of package.

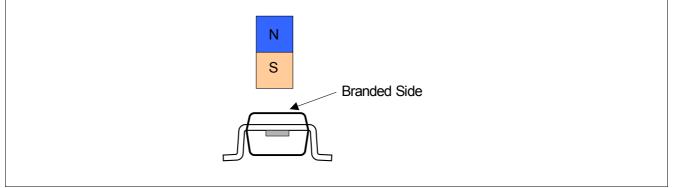


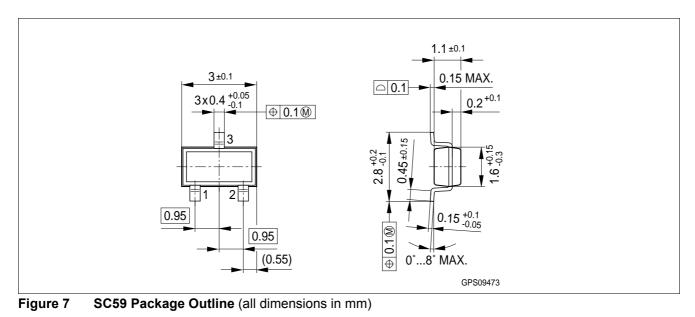
Figure 6 Definition of magnetic field direction



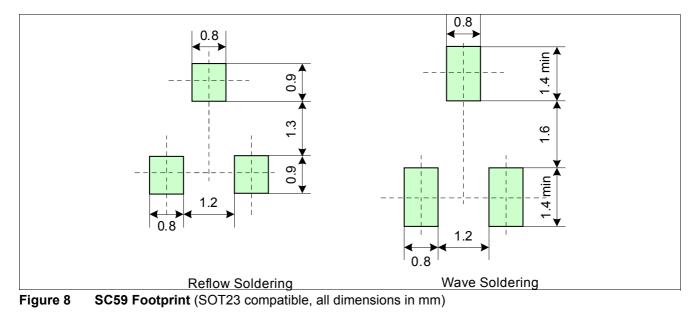
Package Information

4 Package Information

4.1 Package Outline



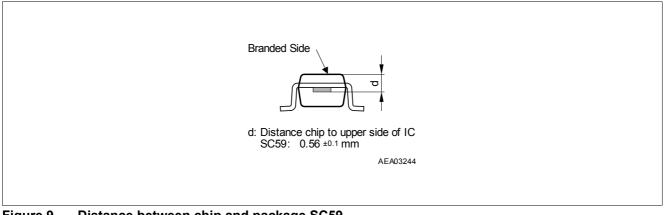
The following picture shows a recommendation for the PCB layout.





Package Information

Distance between Chip and Package 4.2



Distance between chip and package SC59 Figure 9

4.3 **Package Marking**

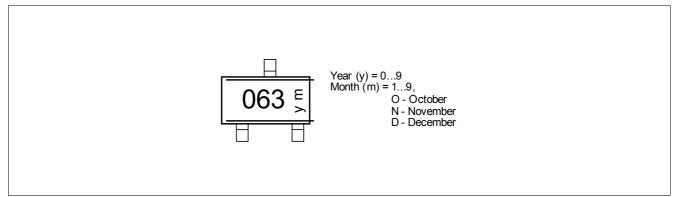


Figure 10 Marking of TLE4906-3K

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